

SNUBBERLESSTM, LOGIC LEVEL & STANDARD

6A TRIACs

Table 1: Main Features

Symbol	Value	Unit
$I_{T(RMS)}$	6	A
V_{DRM}/V_{RRM}	600 and 800	V
$I_{GT}(Q_1)$	5 to 50	mA

DESCRIPTION

Available either in through-hole or surface-mount packages, the **BTA06** and **BTB06** triac series is suitable for general purpose AC switching. They can be used as an ON/OFF function in applications such as static relays, heating regulation, induction motor starting circuits... or for phase control operation in light dimmers, motor speed controllers,...

The snubberless and logic level versions (BTA/BTB...W) are specially recommended for use on inductive loads, thanks to their high commutation performances.

By using an internal ceramic pad, the BTA series provides voltage insulated tab (rated at 2500V_{RMS}) complying with UL standards (File ref.: E81734).

Table 3: Absolute Maximum Ratings

Symbol	Parameter	Value	Unit		
$I_{T(RMS)}$	RMS on-state current (full sine wave)	TO-220AB	$T_c = 110^\circ\text{C}$	6	A
		TO-220AB Ins.	$T_c = 105^\circ\text{C}$		
I_{TSM}	Non repetitive surge peak on-state current (full cycle, T_j initial = 25°C)	F = 50 Hz	t = 20 ms	60	A
		F = 60 Hz	t = 16.7 ms	63	
I^2t	I^2t Value for fusing	$t_p = 10$ ms		21	A ² s
di/dt	Critical rate of rise of on-state current $I_G = 2 \times I_{GT}$, $t_r \leq 100$ ns	F = 120 Hz	$T_j = 125^\circ\text{C}$	50	A/ μ s
I_{GM}	Peak gate current	$t_p = 20$ μ s	$T_j = 125^\circ\text{C}$	4	A
$P_{G(AV)}$	Average gate power dissipation	$T_j = 125^\circ\text{C}$		1	W
T_{stg} T_j	Storage junction temperature range Operating junction temperature range			- 40 to + 150 - 40 to + 125	°C

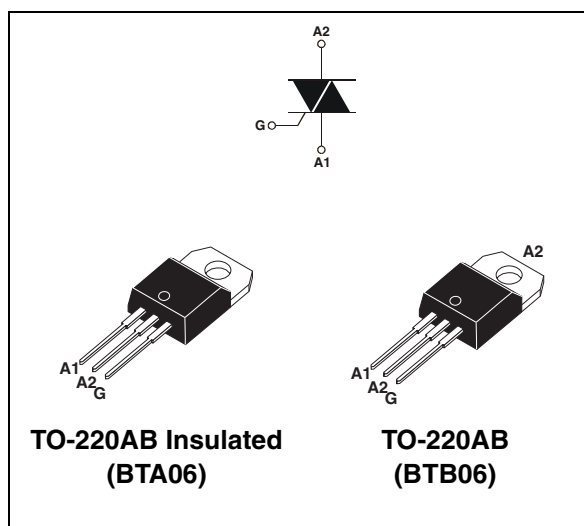


Table 2: Order Codes

Part Number	Marking
BTA06-xxxxxRG	See page table 8 on page 6
BTB06-xxxxxRG	

BTA06 and BTB06 Series

Tables 4: Electrical Characteristics ($T_j = 25^\circ\text{C}$, unless otherwise specified)

■ **SNUBBERLESS and Logic Level (3 quadrants)**

Symbol	Test Conditions	Quadrant		BTA06 / BTB06				Unit
				TW	SW	CW	BW	
I_{GT} (1)	$V_D = 12\text{ V}$ $R_L = 30\ \Omega$	I - II - III	MAX.	5	10	35	50	mA
V_{GT}		I - II - III	MAX.	1.3				V
V_{GD}	$V_D = V_{DRM}$ $R_L = 3.3\ \text{k}\Omega$ $T_j = 125^\circ\text{C}$	I - II - III	MIN.	0.2				V
I_H (2)	$I_T = 100\ \text{mA}$		MAX.	10	15	35	50	mA
I_L	$I_G = 1.2 I_{GT}$	I - III	MAX.	10	25	50	70	mA
		II		15	30	60	80	
dV/dt (2)	$V_D = 67\% V_{DRM}$ gate open $T_j = 125^\circ\text{C}$		MIN.	20	40	400	1000	V/ μs
$(dI/dt)_c$ (2)	$(dV/dt)_c = 0.1\ \text{V}/\mu\text{s}$ $T_j = 125^\circ\text{C}$		MIN.	2.7	3.5	-	-	A/ms
	$(dV/dt)_c = 10\ \text{V}/\mu\text{s}$ $T_j = 125^\circ\text{C}$			1.2	2.4	-	-	
	Without snubber $T_j = 125^\circ\text{C}$			-	-	3.5	5.3	

■ **Standard (4 quadrants)**

Symbol	Test Conditions	Quadrant		BTA06 / BTB06		Unit
				C	B	
I_{GT} (1)	$V_D = 12\text{ V}$ $R_L = 30\ \Omega$	I - II - III IV	MAX.	25 50	50 100	mA
V_{GT}		ALL	MAX.	1.3		V
V_{GD}	$V_D = V_{DRM}$ $R_L = 3.3\ \text{k}\Omega$ $T_j = 125^\circ\text{C}$	ALL	MIN.	0.2		V
I_H (2)	$I_T = 500\ \text{mA}$		MAX.	25	50	mA
I_L	$I_G = 1.2 I_{GT}$	I - III - IV	MAX.	40	50	mA
		II		80	100	
dV/dt (2)	$V_D = 67\% V_{DRM}$ gate open $T_j = 125^\circ\text{C}$		MIN.	200	400	V/ μs
$(dV/dt)_c$ (2)	$(dI/dt)_c = 2.7\ \text{A}/\text{ms}$ $T_j = 125^\circ\text{C}$		MIN.	5	10	V/ μs

Table 5: Static Characteristics

Symbol	Test Conditions			Value	Unit
V_{TM} (2)	$I_{TM} = 8.5\ \text{A}$	$t_p = 380\ \mu\text{s}$	$T_j = 25^\circ\text{C}$	MAX.	1.55 V
V_{t0} (2)	Threshold voltage		$T_j = 125^\circ\text{C}$	MAX.	0.85 V
R_d (2)	Dynamic resistance		$T_j = 125^\circ\text{C}$	MAX.	60 m Ω
I_{DRM} I_{RRM}	$V_{DRM} = V_{RRM}$		$T_j = 25^\circ\text{C}$	MAX.	5 μA
			$T_j = 125^\circ\text{C}$		1 mA

Note 1: minimum I_{GT} is guaranteed at 5% of I_{GT} max.

Note 2: for both polarities of A2 referenced to A1.

Table 6: Thermal resistance

Symbol	Parameter		Value	Unit
$R_{th(j-c)}$	Junction to case (AC)	TO-220AB	1.8	°C/W
		TO-220AB Insulated	2.7	
$R_{th(j-a)}$	Junction to ambient	TO-220AB TO-220AB Insulated	60	°C/W

Figure 1: Maximum power dissipation versus RMS on-state current (full cycle)

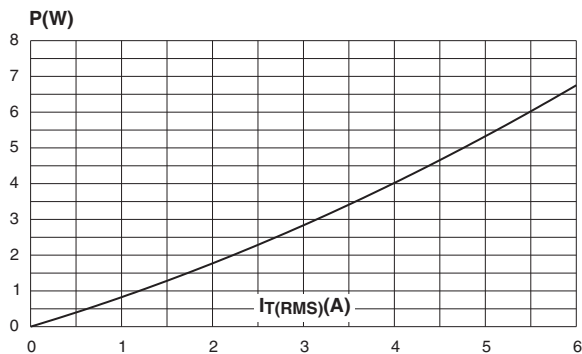


Figure 2: RMS on-state current versus case temperature (full cycle)

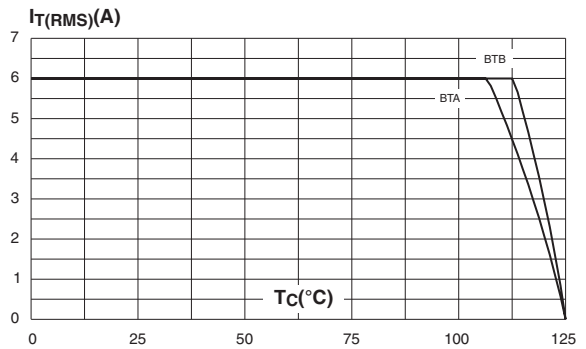


Figure 3: Relative variation of thermal impedance versus pulse duration

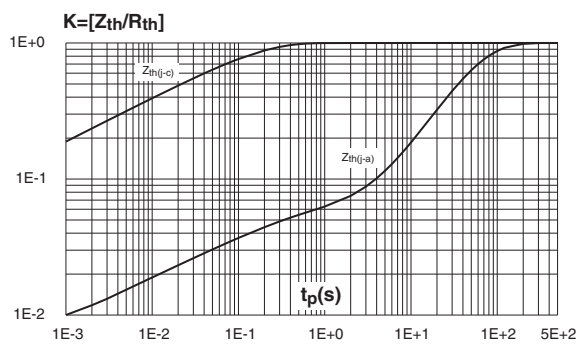
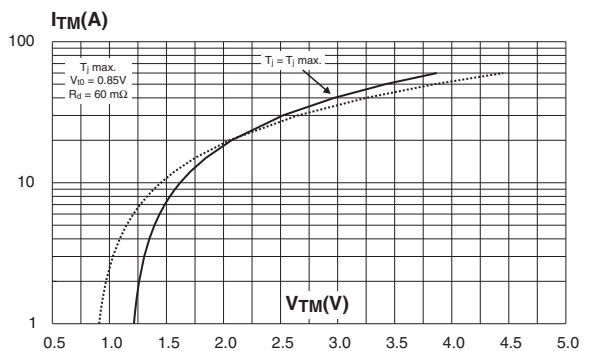


Figure 4: On-state characteristics (maximum values)



BTA06 and BTB06 Series

Figure 5: Surge peak on-state current versus number of cycles

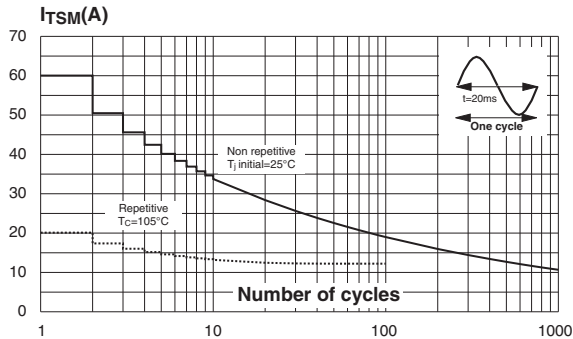


Figure 6: Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 10$ ms and corresponding value of I^2t

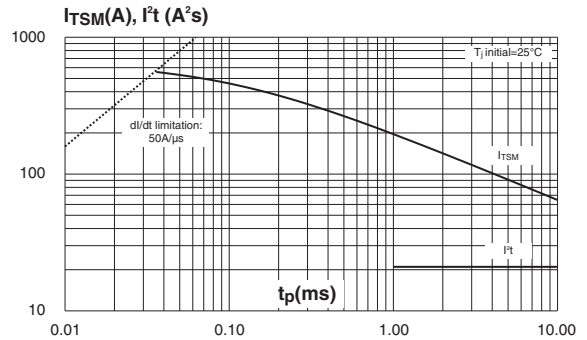


Figure 7: Relative variation of gate trigger current, holding current and latching current versus junction temperature (typical values)

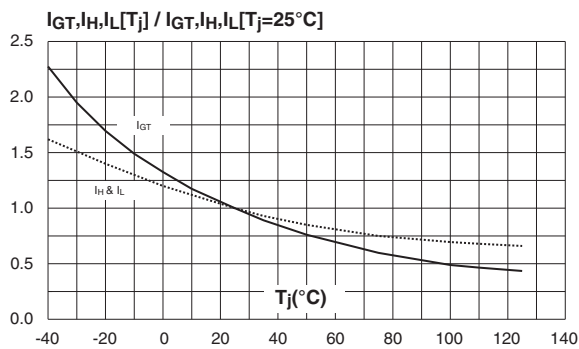


Figure 8: Relative variation of critical rate of decrease of main current versus $(dV/dt)_c$ (typical values) (Snubberless & logic level types)

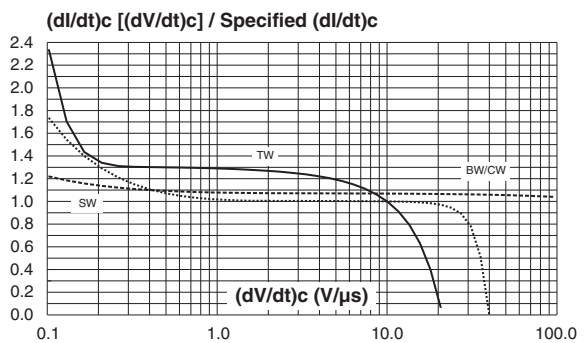


Figure 9: Relative variation of critical rate of decrease of main current versus $(dV/dt)_c$ (typical values) (Standard types)

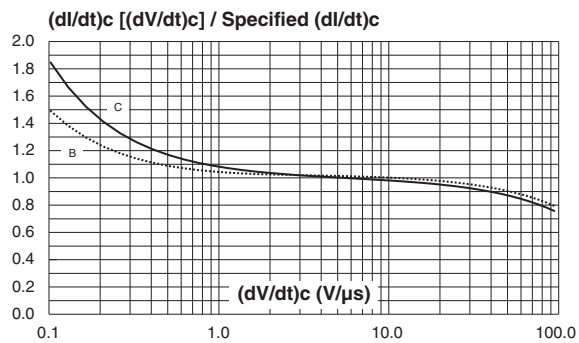


Figure 10: Relative variation of critical rate of decrease of main current versus junction temperature

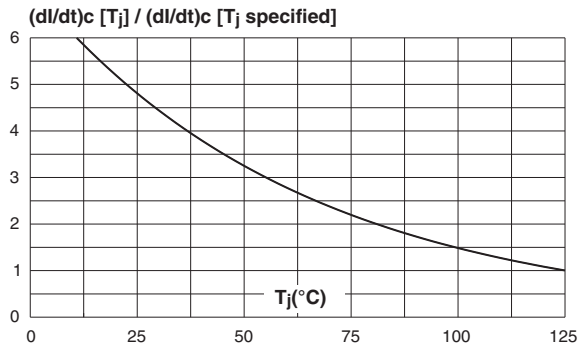


Figure 11: Ordering Information Scheme

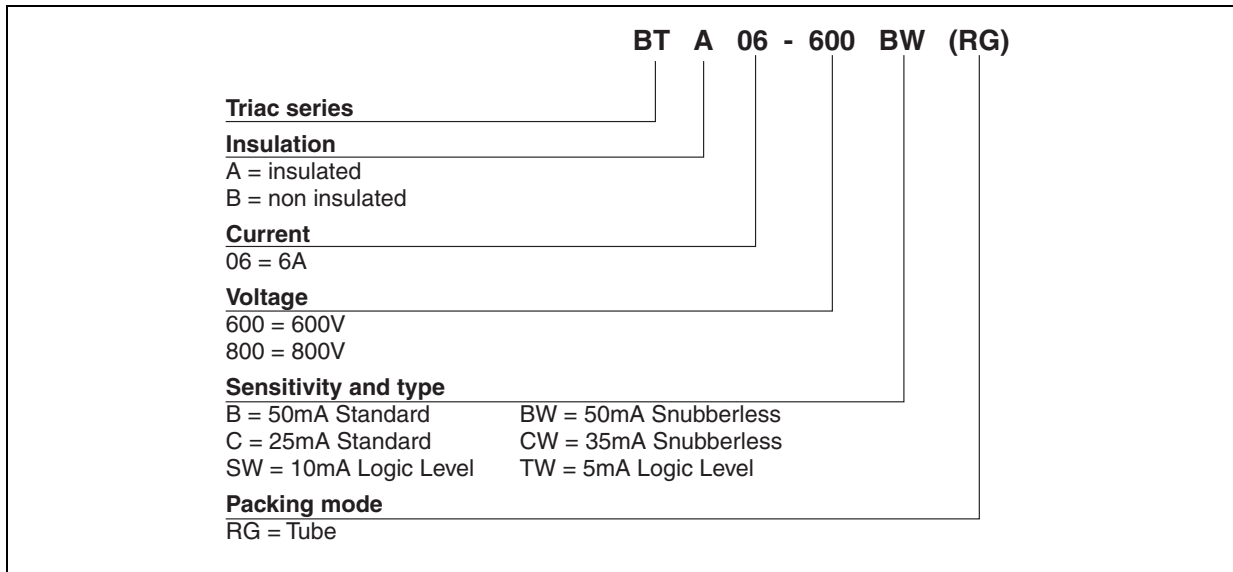


Table 7: Product Selector

Part Number	Voltage (xxx)		Sensitivity	Type	Package
	600 V	800 V			
BTA/BTB06-xxxB	X	X	50 mA	Standard	TO-220AB
BTA/BTB06-xxxBW	X	X	50 mA	Snubberless	TO-220AB
BTA/BTB06-xxxC	X	X	25 mA	Standard	TO-220AB
BTA/BTB06-xxxCW	X	X	35 mA	Snubberless	TO-220AB
BTA/BTB06-xxxSW	X	X	10 mA	Logic level	TO-220AB
BTA/BTB06-xxxTW	X	X	5 mA	Logic Level	TO-220AB

BTB: non insulated TO-220AB package

BTA06 and BTB06 Series

Figure 12: TO-220AB (insulated and non insulated) Package Mechanical Data

